Electronic Supplementary Information

Micron-sized [6,6]-Phenyl C61 butyric acid methyl ester crystals grown by dip coating in solvent vapour atmosphere: interfaces for organic photovoltaics

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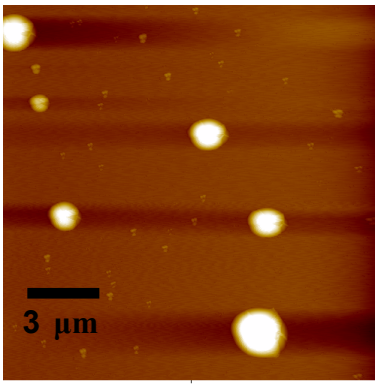

Figure S1: Topographical AFM image of nanoscale amorphous PCBM aggregates on silanized SiO_x formed after dip coating at room temperature (T ≈ 20ºC), z-range; 290nm;

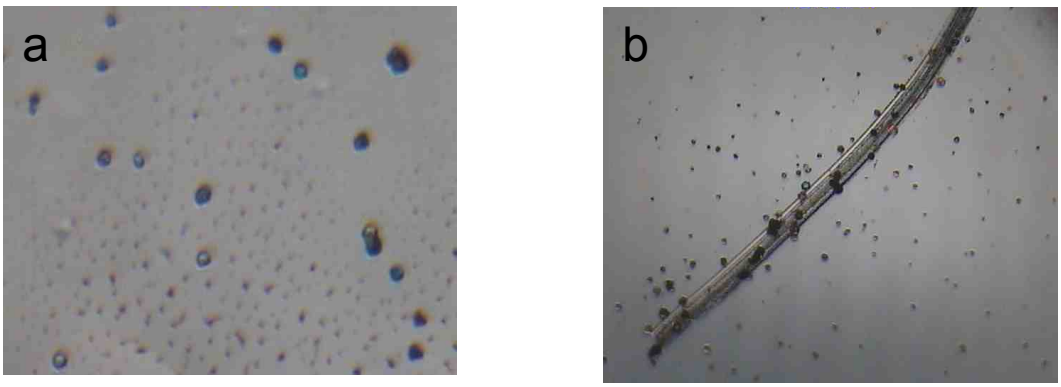

Figure S2: (a) Optical microscopy images of (a) PCBM crystals on SiO_x formed during rapid withdrawal speed; 10 cm/h, grown at 4-10ºC (140 x 125 µm); (b) PCBM crystals on SiO_x forming preferentially along the scratched line, grown at 4-10ºC (520 x 450 µm).

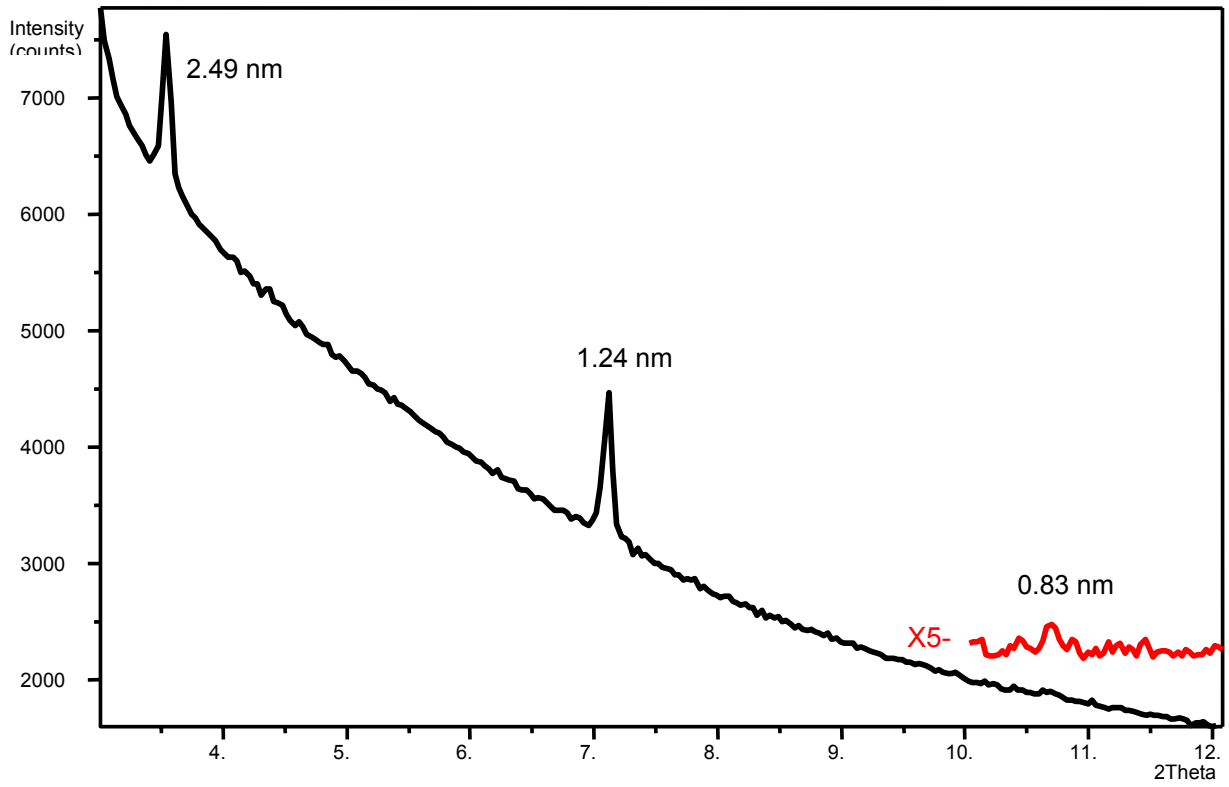

Figure S3: XRD spectrum of PCBM crystals on silanized SiO_x.

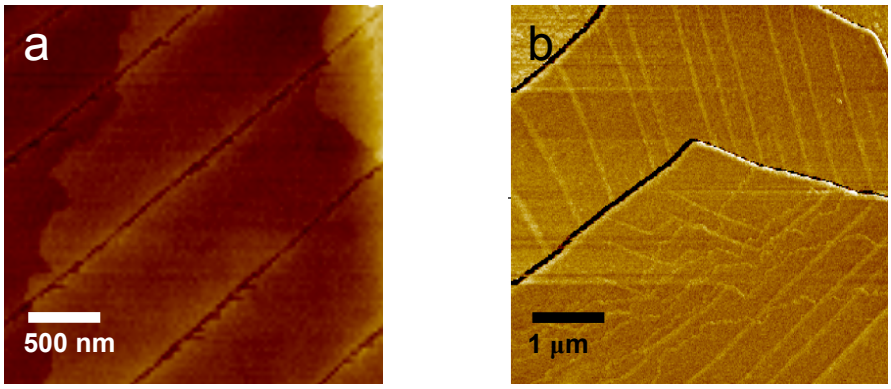

Figure S4: AFM images a) topographical close-up of molecular steps, z-range; 14 nm and b) phase image of crystal in which the straightness of channels and their varying directionality as well as the molecular steps are distinguishable, z-range; 460 nm.